

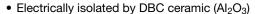
Thyristor/Thyristor, 150 A (INT-A-PAK Power Module)



INT-A-PAK

PRIMARY CHARACTERISTICS				
I _{T(AV)}	150 A			
Туре	Modules - thyristor, standard			
Package	INT-A-PAK			

FEATURES





3500 V_{RMS} isolating voltage

- THINS ISSIAMING VOILAGE
- Industrial standard package
- High surge capability
- · Glass passivated chips
- Simple mounting
- UL approved file E78996
- · Designed and qualified for multiple level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · Battery charges
- Welders
- Power converters

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	VALUES	UNITS				
I _{T(AV)}	85 °C	150	A				
I _{T(RMS)}		330					
1	50 Hz	4000	Α				
ITSM	60 Hz	4200					
2t	50 Hz	80	kA ² s				
1-1	60 Hz	73	KA-S				
I ² √t		800	kA²√s				
V _{DRM} /V _{RRM}		400	V				
T _{Stg}	Range	-40 to +150	°C				
T _J	Range	-40 to +125	C				

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} /V _{DSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA				
VS-VSKT152/04PbF	400	500	50				



ON-STATE CONDUCTION						
PARAMETER	SYMBOL		TEST CONDITIO	NS	VALUES	UNITS
Maximum average on-state current	I	190° conductio	on half sine wave		150	Α
at case temperature	I _{T(AV)}	180 Conductio	on nan sine wave		85	°C
Maximum RMS on-state current	I _{T(RMS)}	As AC switch			330	
		t = 10 ms	No voltage		4000	
Maximum peak, one-cycle on-state, non-repetitive		t = 8.3 ms	reapplied		4200	Α
surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		3350	
S		t = 8.3 ms	reapplied	Sine half wave, initial $T_J = T_J$ maximum	3500	
		t = 10 ms	No voltage		80	kA ² s
Massimos no 12t four francis	I ² t	t = 8.3 ms	reapplied		73	
Maximum I ² t for fusing	1-1	t = 10 ms	100 % V _{RRM}		56	
		t = 8.3 ms	reapplied		51	
Maximum l ² √t for fusing	I²√t	t = 0.1 ms to 10	0 ms, no voltage r	eapplied	800	kA ^{2√} s
Value of threshold voltage	V _{T(TO)}	T manyimay ma			0.82	V
On-state slope resistance	r _t	T _J maximum		1.44	mΩ	
Maximum on-state voltage drop	V_{TM}	$I_{pk} = \pi \times I_{T(AV)}, T_{J} = 25 ^{\circ}C$			1.48	V
Maximum holding current	I _H		ode supply = 6 V, gate open circuit		200	mA
Maximum latching current	ΙL	$T_J = 25$ °C, and	ode supply = 6 V,	resistive load	400	

SWITCHING					
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES	UNITS
Typical delay time	t _{gd}	T _J = 25 °C	Gate current = 1 A, dl _q /dt = 1 A/µs	1	
Typical rise time	t _{gr}	1J = 25 C	Gate current = 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}$	2	μs
Typical turn-off time	t _q	$I_{TM} = 300 \text{ A},$ $V_R = 50 \text{ V}; \text{ d}$	- dl/dt = 15 A/ μ s; T $_J$ = T $_J$ maximum V/dt = 20 V/ μ s; gate 0 V, 100 Ω	50 to 200	μο

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak reverse and off-state leakage current	I _{RRM,} I _{DRM}	T _J = 125 °C	50	mA
RMS insulation voltage	V _{INS}	50 Hz, circuit to base, all terminals shorted, t = 1 s	3500	V
Critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, exponential to 67 % rated V_{DRM}	1000	V/µs



TRIGGERING					
PARAMETER	SYMBOL	TEST CON	IDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}	$t_p \le 5 \text{ ms}, T_J = T_J \text{ maxim}$	um	12	W
Maximum average gate power	P _{G(AV)}	$f = 50 \text{ Hz}, T_J = T_J \text{ maxim}$	um	3	VV
Maximum peak gate current	I _{GM}			3	А
Maximum peak negative gate voltage	- V _{GT}	$t_p \le 5$ ms, $T_J = T_J$ maxim	$t_p \le 5 \text{ ms}, T_J = T_J \text{ maximum}$		
		T _J = - 40 °C		4	V
Maximum required DC gate voltage to trigger	V_{GT}	T _J = 25 °C		2.5	
voltage to trigger		T _J = T _J maximum	Anode supply = 6 V,	1.7	
		T _J = - 40 °C	resistive load; $R_a = 1 \Omega$	270	
Maximum required DC gate current to trigger	I _{GT}	T _J = 25 °C		150	mA
		$T_J = T_J$ maximum		80	
Maximum gate voltage that will not trigger	V_{GD}	$T_J = T_J$ maximum, rated V_{DRM} applied		0.3	V
Maximum gate current that will not trigger	I _{GD}			10	mA
Maximum rate of rise of turned-on current	dl/dt	$T_J = T_J$ maximum, $I_{TM} = 4$	100 A rated V _{DRM} applied	300	A/μs

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction operating temperature range	T _J		-40 to +125	°C			
Maximum storage temperature range	T _{Stg}		-40 to +150	O			
Maximum thermal resistance, junction to case per junction	R _{thJC}	DC operation	0.18	K/W			
Maximum thermal resistance, case to heatsink per module	R _{thCS}	Mounting surface smooth, flat and greased	0.05	r./ vv			
Mounting IAP to heatsink torque ± 10 % busbar to IAP		A mounting compound is recommended and the torque should be rechecked after a period of	4 to 6	Nm			
Annyayimata waight		3 hours to allow for the spread of the compound.	200	g			
Approximate weight		Lubricated threads.	7.1	oz.			
Case style	ase style		INT-A-	PAK			

∆R CONDUCTI	ON PE	R JUNC	CTION								
DEVICES	SINUSOIDAL CONDUCTION AT T _J MAXIMUM				I	RECTANGULAR CONDUCTION AT T _J MAXIMUM				N	UNITS
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
VSKT152/04PbF	0.007	0.010	0.013	0.016	0.017	0.009	0.012	0.014	0.016	0.017	K/W

Note

• Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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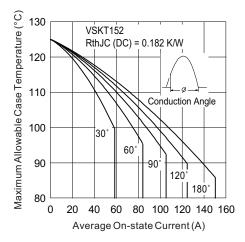


Fig. 1 - Current Ratings Characteristics

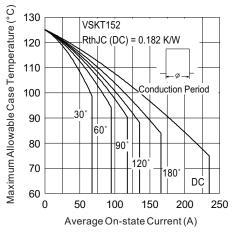


Fig. 2 - Current Ratings Characteristics

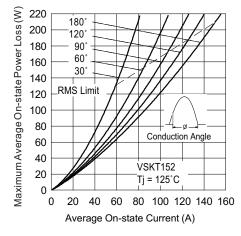


Fig. 3 - Forward Power Loss Characteristics

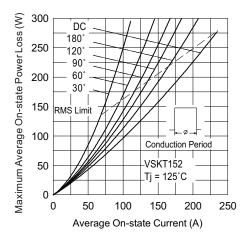


Fig. 4 - Forward Power Loss Characteristics

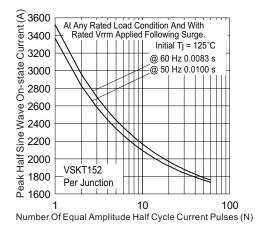


Fig. 5 - Maximum Non-Repetitive Surge Current

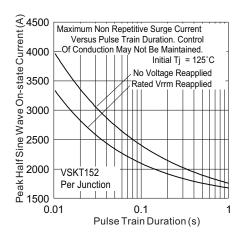


Fig. 6 - Maximum Non-Repetitive Surge Current

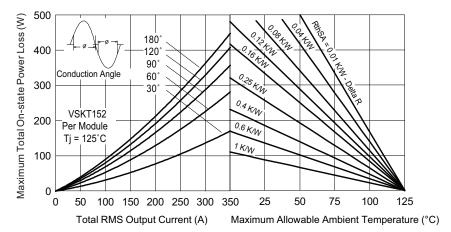


Fig. 7 - On-State Power Loss Characteristics

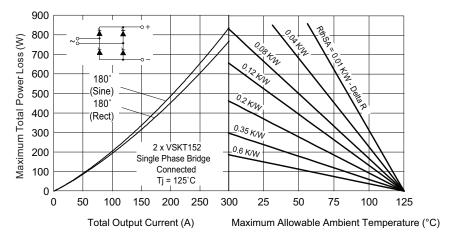


Fig. 8 - On-State Power Loss Characteristics

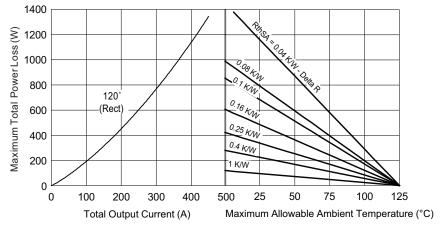


Fig. 9 - On-State Power Loss Characteristics

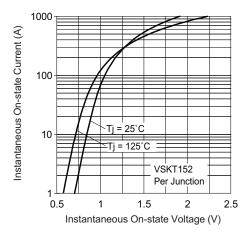


Fig. 10 - On-State Voltage Drop Characteristics

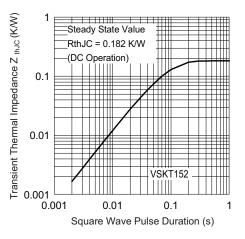


Fig. 11 - Thermal Impedance Z_{thJC} Characteristics

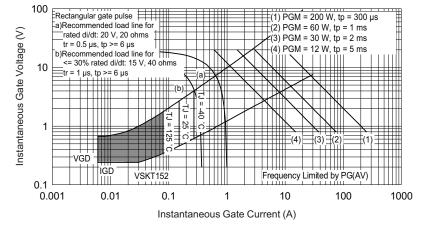
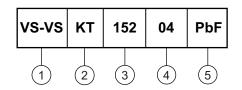


Fig. 12 - Gate Characteristics



ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

Circuit configuration

Current rating

4 - Voltage rating (04 = 400 V)

5 - PbF = Lead (Pb)-free

Note

• To order the optional hardware go to www.vishay.com/doc?95172

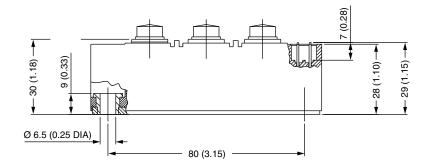
CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs doubler circuit	Т	10~ 20+ NO 100 100 100 100 100 100 100 100 100 10

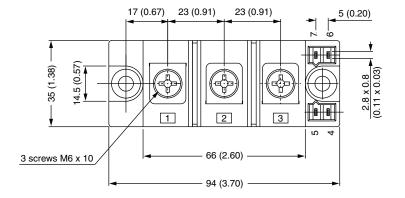
LINKS TO REL	ATED DOCUMENTS
Dimensions	www.vishay.com/doc?95067

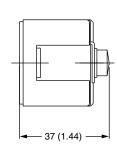


INT-A-PAK IGBT/Thyristor

DIMENSIONS in millimeters (inches)









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Vishay

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